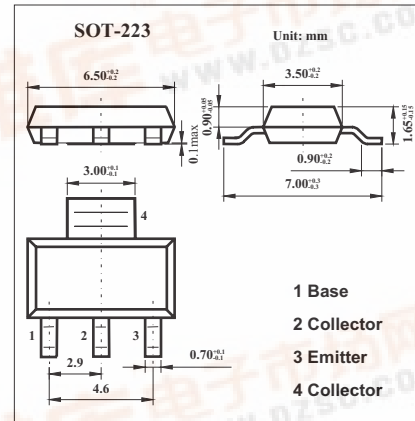


SMD Type Transistors

High Voltage Transistor  
PZTA96S

- Features
- PNP Silicon



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Emmitter Voltage	V <sub>CEO</sub>	-450	V
Collector-Base Voltage	V <sub>CBO</sub>	-450	V
Emmitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-500	mA
Total Power Dissipation Up to TA = 25°C *	P <sub>D</sub>	1.5	Watts
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C
Junction Temperature	T <sub>J</sub>	150	°C
Thermal Resistance from Junction to Ambient *	R <sub>θJA</sub>	83.3	°C

\* Device mounted on a glass epoxy printed circuit board 1.575 in. X 1.575 in.X 0.059 in.;

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Emmitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -1.0 mA, I <sub>B</sub> = 0	-450			V
Collector-Emmitter Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -100 μA, I <sub>E</sub> = 0	-450			V
Emmitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -10μA, I <sub>C</sub> = 0	-5.0			V
Collector-Base Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> = -400 V, I <sub>E</sub> = 0			-0.1	μA
Emmitter-Base Cutoff Current	I <sub>EBO</sub>	V <sub>BE</sub> = -4.0 V, I <sub>C</sub> = 0			-0.1	μA
DC Current Gain*	h <sub>FE</sub>	I <sub>C</sub> = -10 mA, V <sub>CE</sub> = -10 V	50		150	
Saturation Voltages	V <sub>CE(sat)</sub>	I <sub>C</sub> = -20 mA, I <sub>B</sub> = -2.0 mA			-0.6	V
	V <sub>BE(sat)</sub>	I <sub>C</sub> = -20 mA, I <sub>B</sub> = -2.0 mA			-1.0	V

\* Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle = 2.0%.

■ Marking

Marking	ZTA96
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